Jan van den Hurk

List of Publications by Year in descending order

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1039406 1281420 12 995 9 11 citations h-index g-index papers 14 14 14 1530 docs citations times ranked citing authors all docs

#	Article	IF	CITATIONS
1	Redox Reactions at Cu,Ag/Ta ₂ O ₅ Interfaces and the Effects of Ta ₂ O ₅ Film Density on the Forming Process in Atomic Switch Structures. Advanced Functional Materials, 2015, 25, 6374-6381.	7.8	148
2	Realization of Boolean Logic Functionality Using Redoxâ€Based Memristive Devices. Advanced Functional Materials, 2015, 25, 6414-6423.	7.8	127
3	A compact and low-weight sputtering unit for in situ investigations of thin film growth at synchrotron radiation beamlines. Review of Scientific Instruments, 2015, 86, 053906.	0.6	4
4	Processes and Limitations during Filament Formation and Dissolution in GeS _{<i>x</i>>} -based ReRAM Memory Cells. Journal of Physical Chemistry C, 2015, 119, 18678-18685.	1.5	20
5	(Keynote) Atomic Scale and Interface Interactions in Redox-Based Resistive Switching Memories. ECS Transactions, 2014, 64, 3-18.	0.3	8
6	Volatile resistance states in electrochemical metallization cells enabling non-destructive readout of complementary resistive switches. Nanotechnology, 2014, 25, 425202.	1.3	64
7	Physical origins and suppression of Ag dissolution in GeS _x -based ECM cells. Physical Chemistry Chemical Physics, 2014, 16, 18217.	1.3	30
8	Preparation and characterization of GeSx thin-films for resistive switching memories. Thin Solid Films, 2013, 527, 299-302.	0.8	22
9	Nanobatteries in redox-based resistive switches require extension of memristor theory. Nature Communications, 2013, 4, 1771.	5.8	473
10	Simulation of polarity independent RESET in electrochemical metallization memory cells. , 2013, , .		13
11	Ag/GeSx/Pt-based complementary resistive switches for hybrid CMOS/Nanoelectronic logic and memory architectures. Scientific Reports, 2013, 3, 2856.	1.6	44
12	Direct Observation of Charge Transfer in Solid Electrolyte for Electrochemical Metallization Memory. Advanced Materials, 2012, 24, 4552-4556.	11,1	42